

Lms43PD-03-R

Device parameters	Symbol	Value	Units
Sensitive area size	d	0.3	mm
Reverse voltage	V_r	0.1	V
Operating/ storage temperature	T_{opr}/T_{stg}	-60+90*	°C
Soldering temperature (can be applied for not more than 5 secs)	T _{sol}	+180	°C



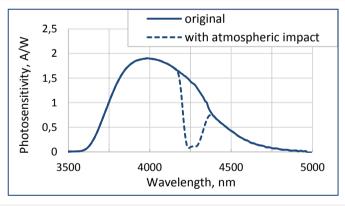
^{*}Photodiode design for different storage/operating temperature range can be considered under request.

All parameters refer to photodiode operation at ambient temperature 25°C unless otherwise stated.

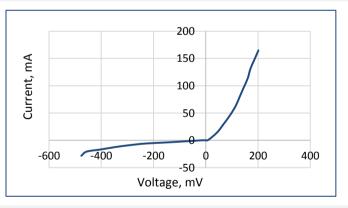
Photodiode parameters	Conditions	Symbol	Value	Units
Cut-off wavelength (at 10% level) ¹	-	λ_{cut}	4.6 - 4.7	μm
Max. sensitivity range (at 80% level) ¹	-	λ_{p}	3.8 - 4.2	μm
Dark current (typical/ maximal) ²	$V_r = 0.1 V$	I _d	typ 4.0 / max 6.0	mA
Shunt resistance (minimal/ typical) ²	$V_r = 10 \text{ mV}$	R_{sh}	min 10 / typ 20	Ω
Capacitance (typical/ maximal) ¹	$V_r = 10 \text{ mV}$	С	-	pF
Photosensitivity (minimal/ typical) ²	$\lambda = 4.1 \mu m$	S	min 1.6 / typ 2.0	A/W
Noise equivalent power (typical/ maximal) ²	λ = 4.1 μ m	NEP	typ 1.4*10 ⁻¹¹ / max 2.5*10 ⁻¹¹	W/Hz ^{1/2}
Detectivity (minimal/ typical) ²	λ = 4.1 μ m	D*	min 1.2*10° / typ 2.1*10°	cm [·] Hz ^{1/2} ·W ⁻¹

¹ Parameter tested for representative sampling.

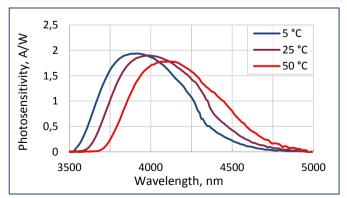
Typical spectral response



Typical current-voltage characteristic



Temperature shift of spectral response



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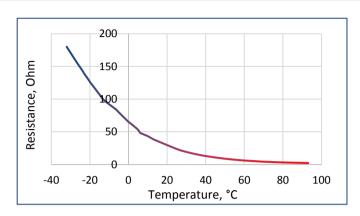
² Parameter tested for each device.



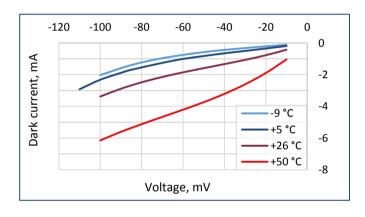
Dark current vs. temperature (Vr = 0.1 V)

-40 -20 0 20 40 60 80 100 We the second of the second of

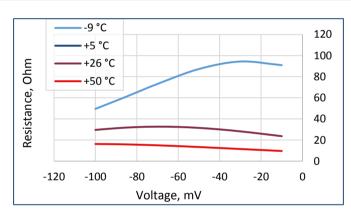
Shunt resistance vs. temperature (Vr = 10 mV)



Dark current vs. voltage



Shunt resistance vs. voltage





Mid-Infrared (MIR) Photodiode

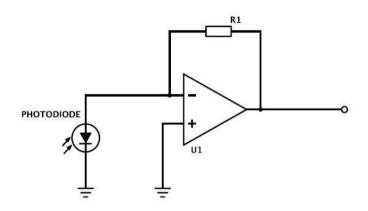
Packages*	Model
TO-18 with a cap without a glass window	Lms43PD-03
TO-18 with a parabolic reflector without a glass window	Lms43PD-03-R
TO-18 with a parabolic reflector with a glass window	Lms43PD-03-RW
TO-5 with a built-in thermocooler and thermoresistor, covered by a cap with a glass window	Lms43PD-03-TEM
TO-5 with a built-in thermocooler and thermoresistor, covered by a parabolic reflector with a glass window	Lms43PD-03-TEM-R
PD with a built-in preamplifier; TO-18 with a parabolic reflector without a window in an aluminum tube	Lms43PD-03-R-PA
PD with a built-in preamplifier; TO-18 with a parabolic reflector with a window in an aluminum tube	Lms43PD-03-RW-PA

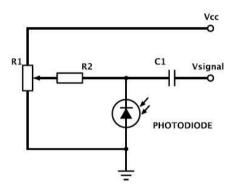
^{*}Standard photodiode packaging is non-hermetical, so that condensation during device operation and storage must be prevented.

Recommended modes of PD operation

PD used as a current source (photovoltaic mode)

PD used in a photoconductive mode (under reverse bias)





We recommend using **photovoltaic mode**, when PD is used under no reverse bias. Use photoconductive mode (mode with reverse bias) with caution.

IMPORTANT CAUTIONS:

- please check your connection circuit before turning on the PD;
- please mind the PD polarity: PD anode is marked with a RED dot;
- please do not connect the PD to the multimeter.

Related products:

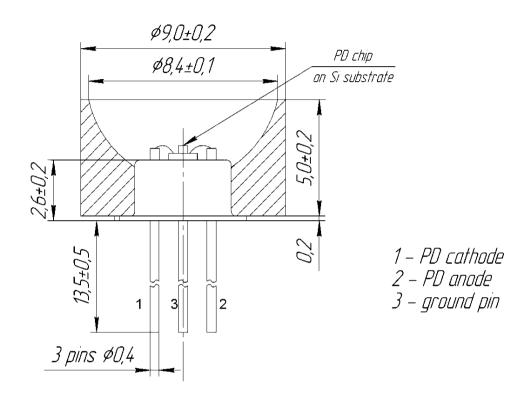
- Light emitting diodes (LEDs) sources of IR radiation;
- PAb preamplifier amplifies photocurrent generated by a PD and converts it into a voltage signal;
- **SDM synchronous detector** enables synchronous operation of a PD coupled with a preamplifier and an LED coupled with a driver; performs convertion of an output PD preamplifier signal into DC voltage signal.

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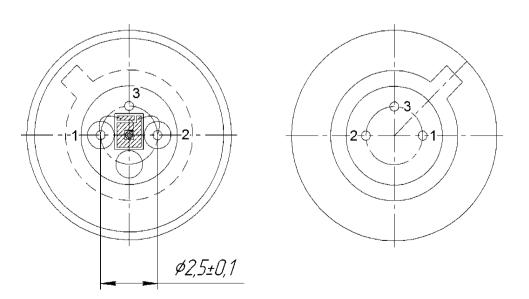
Technical Drawings

Lms43PD-03-R



TOP VIEW

BOTTOM VIEW



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